

ABSTRACT OF THE DISCLOSURE

A semiconductor device includes a non-single-crystal semiconductor film, a support substrate that supports the non-single-crystal semiconductor film,
5 and an active device having a part of the non-single-crystal semiconductor film as a channel region.

In particular, the channel region has an oxygen concentration not higher than 1×10^{18} atoms/cm³ and a carbon concentration not higher than $1 \times$
10 10^{18} atoms/cm³.